

**HIGH VOLTAGE POWER SCHOTTKY RECTIFIER    MBR20150SC**

**General Description**

High voltage dual Schottky rectifier suited for switch mode power supplies and other power converters. This device is intended for use in medium voltage operation, and particularly, in high frequency circuits where low switching losses and low noise are required.

The MBR20150SC is available in standard TO-220F-3, TO-220-3 and TO-220-3 (2) packages.

**Features**

- High Surge Capacity
- 150°C Operating Junction Temperature
- 20A Total (10A Per Diode Leg)
- Guard-ring for Stress Protection
- Pb-free Packages are available

**Main Product Characteristics**

$I_{F(AV)}$	2×10A
$V_{RRM}$	150V
$T_J$	150°C
$V_{F(max)}$	0.75V

**Mechanical Characteristics**

- Case: Epoxy, Molded
- Epoxy Meets UL 94V-0@ 0.125in.
- Weight (Approximately): 1.9Grams
- Finish: All External Surfaces Corrosion Resistant and Terminal
- Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 Seconds

**Applications**

- Power Supply – Output Rectification
- Power Management
- Instrumentation

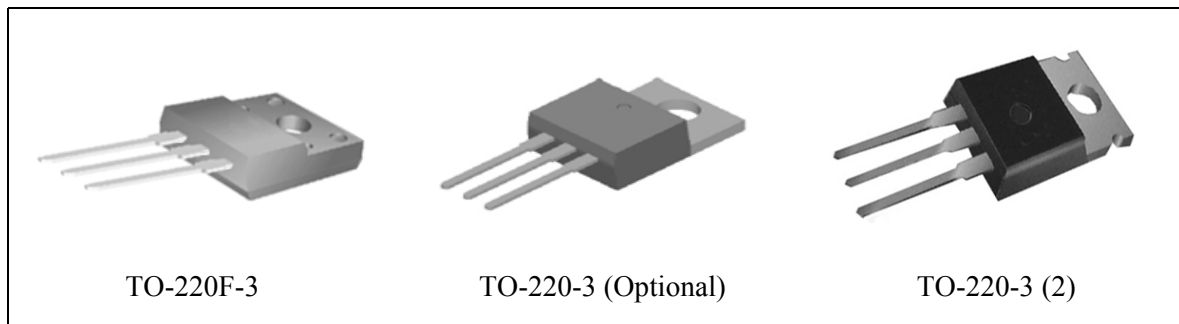


Figure 1. Package Types of MBR20150SC

**HIGH VOLTAGE POWER SCHOTTKY RECTIFIER MBR20150SC**

**Pin Configuration**

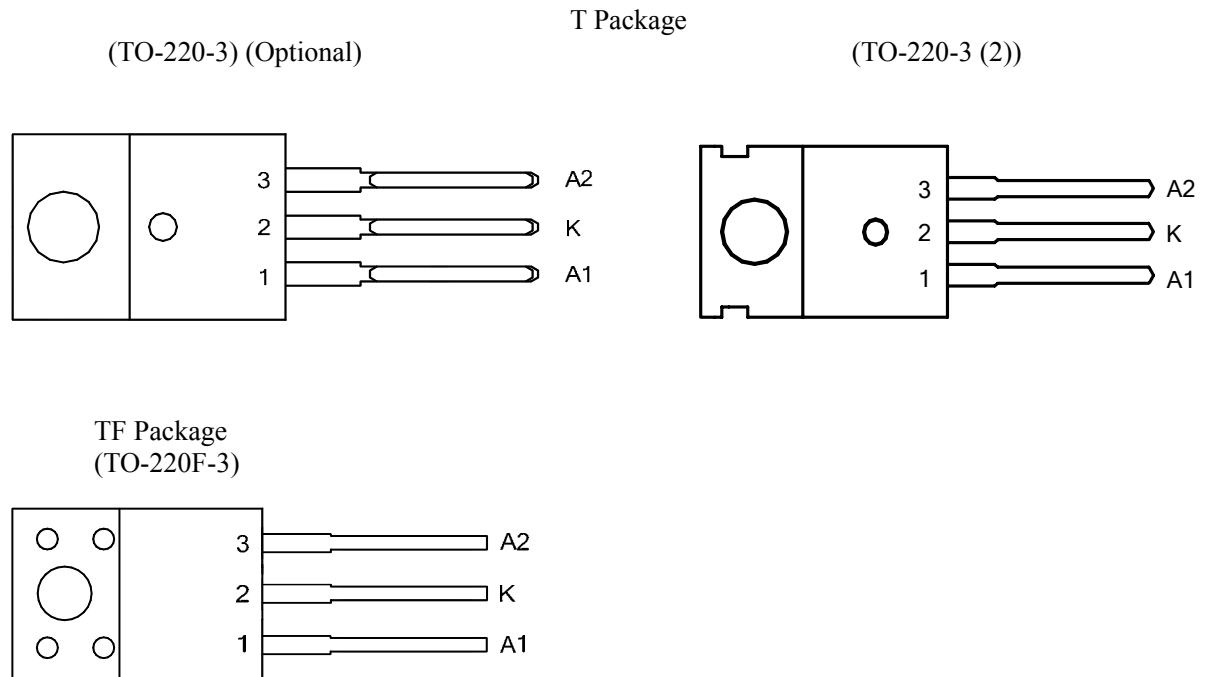


Figure 2. Pin Configuration of MBR20150SC (Top View)

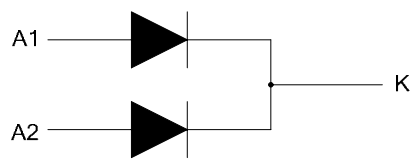
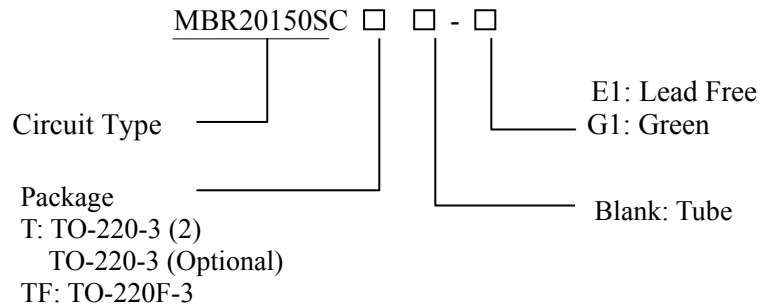


Figure 3. Internal Structure of MBR20150SC

**HIGH VOLTAGE POWER SCHOTTKY RECTIFIER    MBR20150SC**

**Ordering Information**



Package	Part Number		Marking ID		Packin g Type
	Lead Free	Green	Lead Free	Green	
TO-220-3 (2)	MBR20150SCT-E1	MBR20150SCT-G1	MBR20150SCT-E1	MBR20150SCT-G1	Tube
TO-220F-3	MBR20150SCTF-E1	MBR20150SCTF-G1	MBR20150SCTF-E1	MBR20150SCTF-G1	Tube

BCD Semiconductor's Pb-free products, as designated with "E1" suffix in the part number, are RoHS compliant. Products with "G1" suffix are available in green packages.

**Absolute Maximum Ratings ( Per Diode Leg) (Note 1)**

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	150	V
Average Rectified Forward Current (Rated $V_R$ ) $T_C=134^{\circ}C$	$I_{F(AV)}$	10	A
Peak Repetitive Forward Current (Rated $V_R$ , Square Wave, 20kHz) $T_C=133^{\circ}C$	$I_{FRM}$	20	A
Non repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Half Wave, Single Phase, 60Hz)	$I_{FSM}$	150	A
Operating Junction Temperature Range (Note 2)	$T_J$	150	$^{\circ}C$
Storage Temperature Range	$T_{STG}$	-55 to 150	$^{\circ}C$
Voltage Rate of Change (Rated $V_R$ )	dv/dt	10000	V/ $\mu$ s
ESD (Machine Model=C)		>400	V
ESD (Human Body Model=3B)		>8000	V

Note 1: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to "Absolute Maximum Ratings" for extended periods may affect device reliability.

Note 2: The heat generated must be less than the thermal conductivity from Junction-to-Ambient:  $dP_D/dT_J < 1/\theta_{JA}$ .

**HIGH VOLTAGE POWER SCHOTTKY RECTIFIER    MBR20150SC****Recommended Operating Conditions**

Parameter	Symbol	Condition	Value		Unit
Maximum Thermal Resistance	$\theta_{JC}$	Junction to Case	TO-220-3/ TO-220-3 (2)	2.0	°C/W
			TO-220F-3	3.0	
	$\theta_{JA}$	Junction Ambient            to	TO-220-3/ TO-220-3 (2)	60	
			TO-220F-3	60	

**Electrical Characteristics**

Parameter	Symbol	Conditions	Value	Unit
Maximum Instantaneous Forward Voltage Drop (Note 3)	$V_F$	$I_F=10A, T_C=25^\circ C$	0.9	V
		$I_F=10A, T_C=125^\circ C$	0.75	
Maximum Instantaneous Reverse Current (Note 3)	$I_R$	Rated DC Voltage, $T_C=125^\circ C$	20	mA
		Rated DC Voltage, $T_C=25^\circ C$	0.05	

Note 3: Pulse Test: Pulse Width=300 $\mu$ s, Duty Cycle $\leq$ 2.0%.

**HIGH VOLTAGE POWER SCHOTTKY RECTIFIER    MBR20150SC**

**Typical Performance Characteristics**

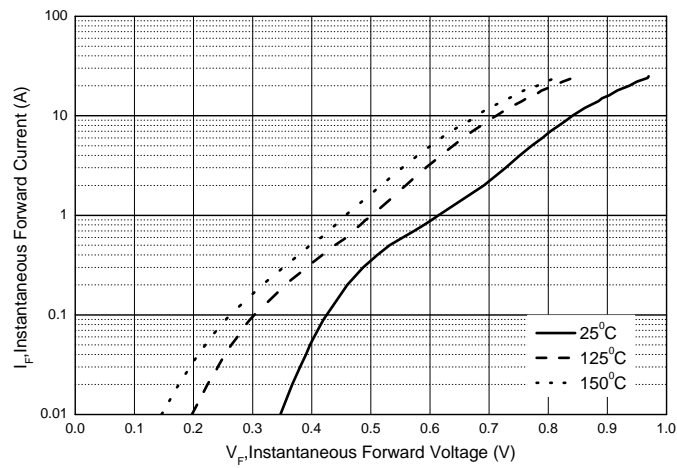


Figure 4. Typical Forward Voltage Per Diode

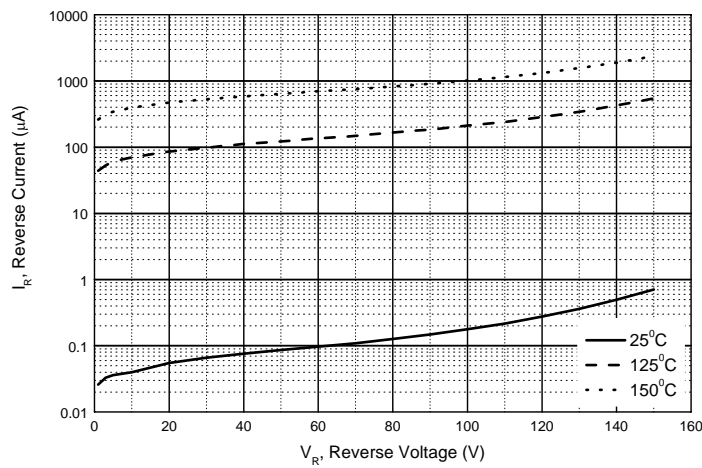


Figure 5. Typical Reverse Current Per Diode

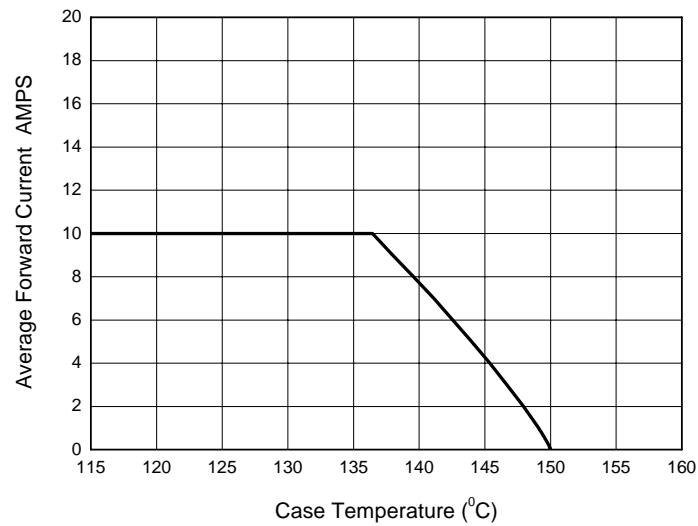
**Typical Performance Characteristics (Continued)**

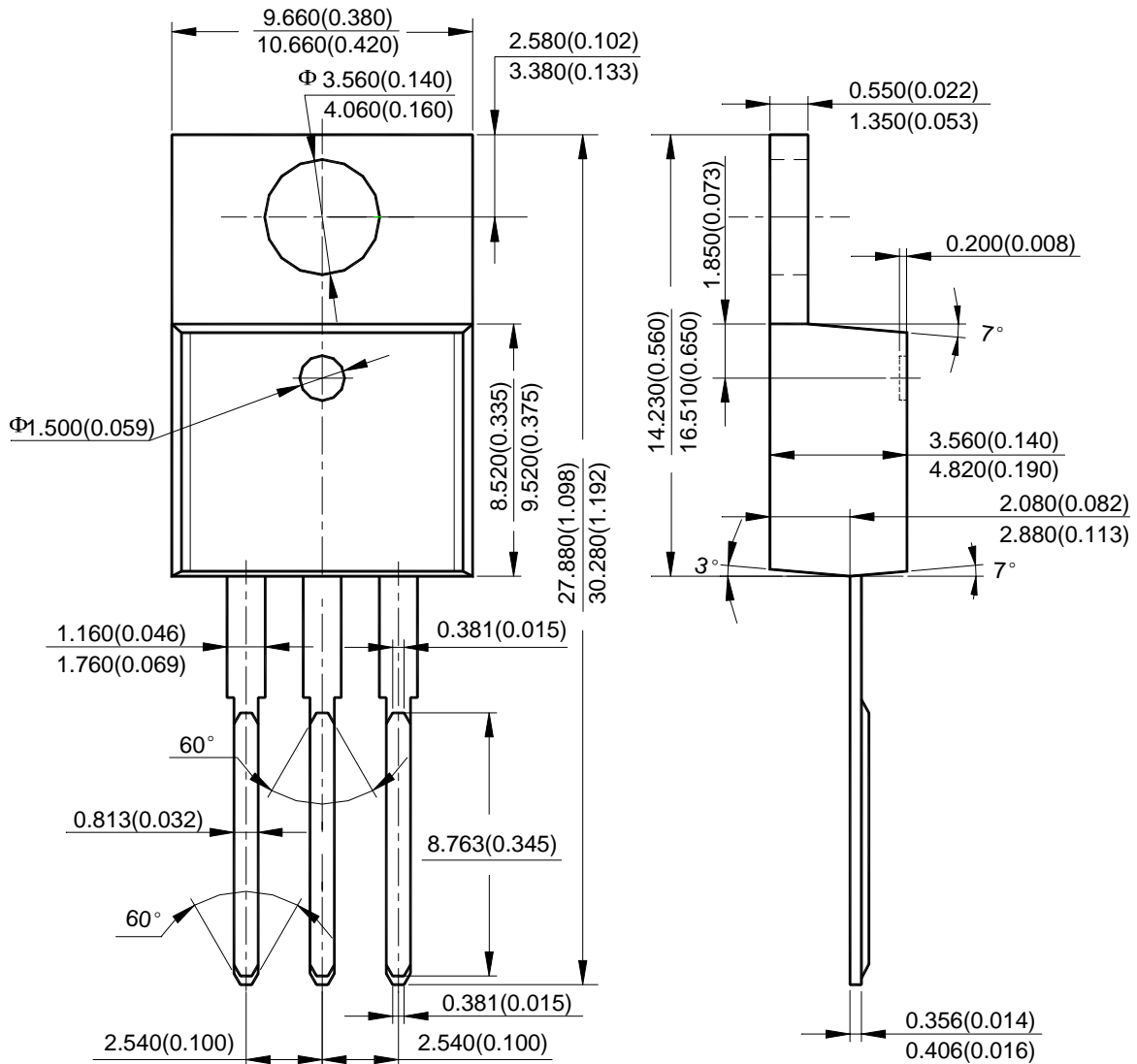
Figure6. Average Forward Current vs. Case Temperature (Square, Per Diode)

**HIGH VOLTAGE POWER SCHOTTKY RECTIFIER MBR20150SC**

**Mechanical Dimensions**

**TO-220-3**  
(Optional)

**Unit: mm(inch)**

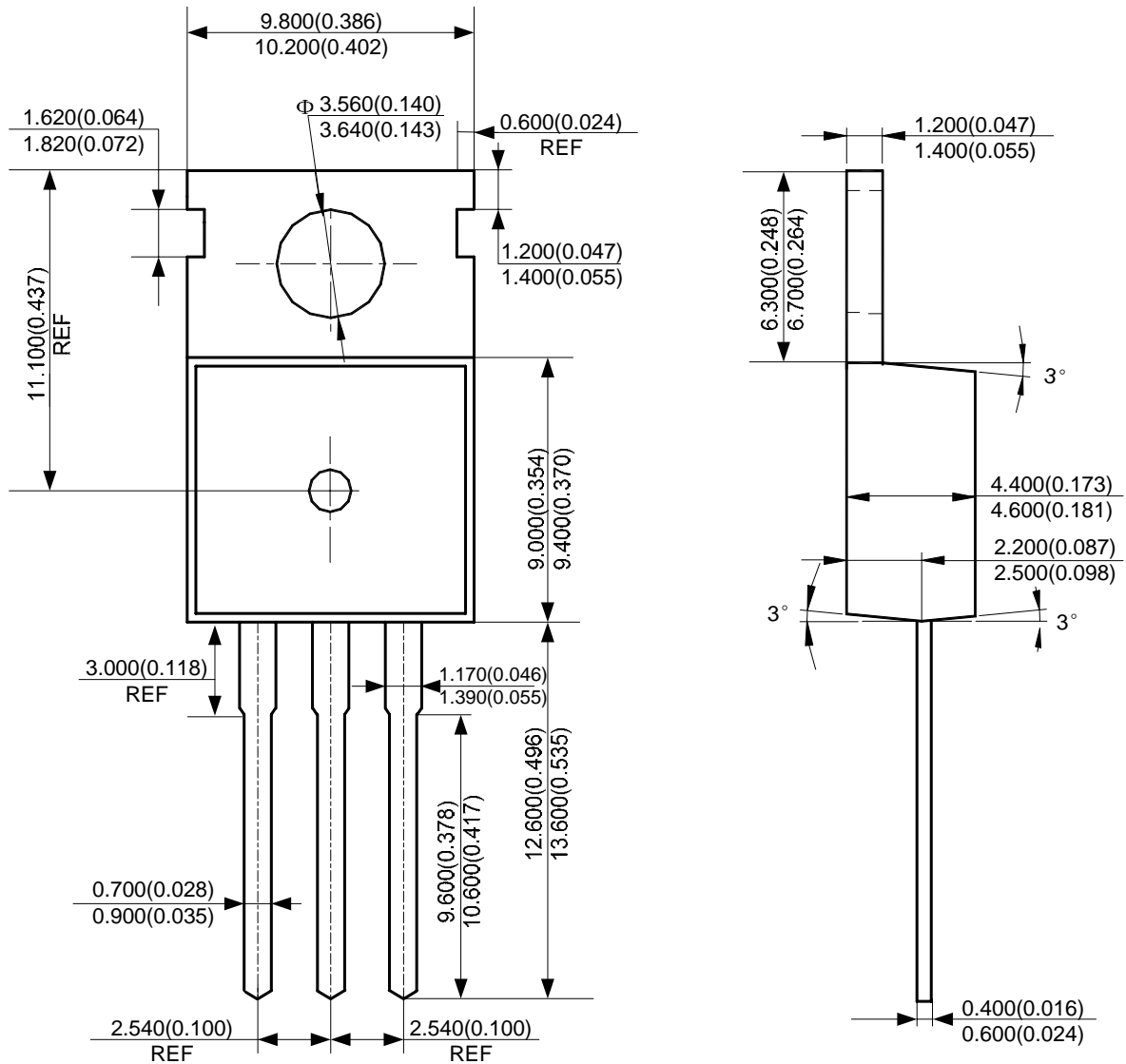


**HIGH VOLTAGE POWER SCHOTTKY RECTIFIER    MBR20150SC**

**Mechanical Dimensions (Continued)**

**TO-220-3 (2)**

**Unit: mm(inch)**



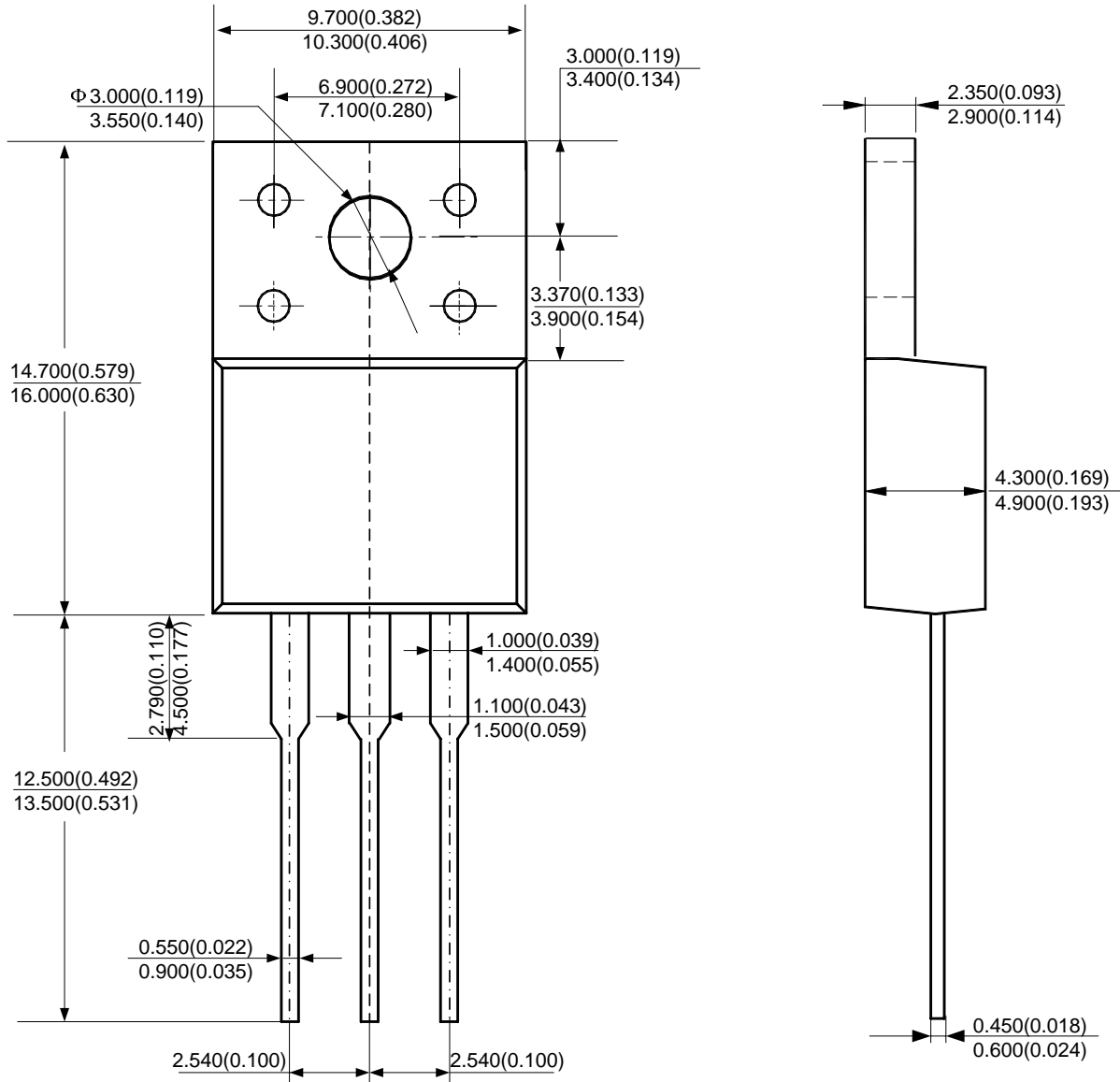


**HIGH VOLTAGE POWER SCHOTTKY RECTIFIER    MBR20150SC**

**Mechanical Dimensions (Continued)**

**TO-220F-3**

**Unit: mm(inch)**





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